

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.085
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.130
I_D (A)	4.4
Configuration	Single

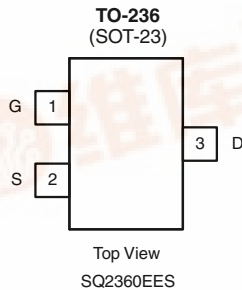
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^c
- Typical ESD Protection 800 V
- Compliant to RoHS Directive 2002/95/EC

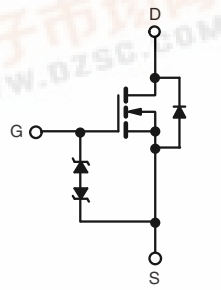
AUTOMOTIVE
GRADE



RoHS
COMPLIANT
HALOGEN
FREE



Marking Code: 8Mxxx



ORDERING INFORMATION

Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2360EES-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	4.4	A
		2.5	
Continuous Source Current (Diode Conduction)	I_S	3.7	
Pulsed Drain Current ^a	I_{DM}	17	
Single Pulse Avalanche Current	I_{AS}	6	mJ
Single Pulse Avalanche Energy	E_{AS}	1.8	
Maximum Power Dissipation ^a	P_D	3	W
		1	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	166	°C/W
Junction-to-Foot (Drain)	R_{thJF}	50	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



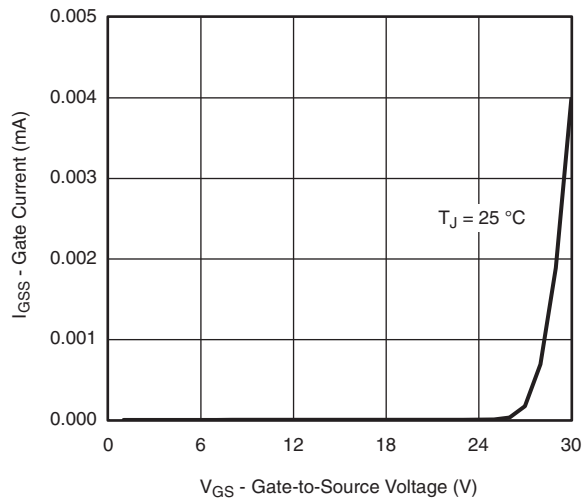
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	-	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 5.5	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	10	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 6 A, T _J = 25 °C	-	0.058	0.085	Ω
		V _{GS} = 10 V	I _D = 6 A, T _J = 125 °C	-	-	0.197	
		V _{GS} = 10 V	I _D = 6 A, T _J = 175 °C	-	-	0.258	Ω
		V _{GS} = 4.5 V	I _D = 5 A	-	0.081	0.130	
Forward Transconductance ^b	g _{fs}	V _{DS} = - 15 V, I _D = 1.9 A		-	5.8	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	295	370	pF
Output Capacitance	C _{oss}			-	55	70	
Reverse Transfer Capacitance	C _{rss}			-	35	55	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 2 A	-	7.40	12	nC
Gate-Source Charge ^c	Q _{gs}			-	0.95	-	
Gate-Drain Charge ^c	Q _{gd}			-	1.94	-	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 15 Ω I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω		-	5	8	ns
Rise Time ^c	t _r			-	11	17	
Turn-Off Delay Time ^c	t _{d(off)}			-	10	15	
Fall Time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	17	A
Forward Voltage	V _{SD}	I _F = 1.5 A, V _{GS} = 0 V		-	0.8	1.2	V

Notes

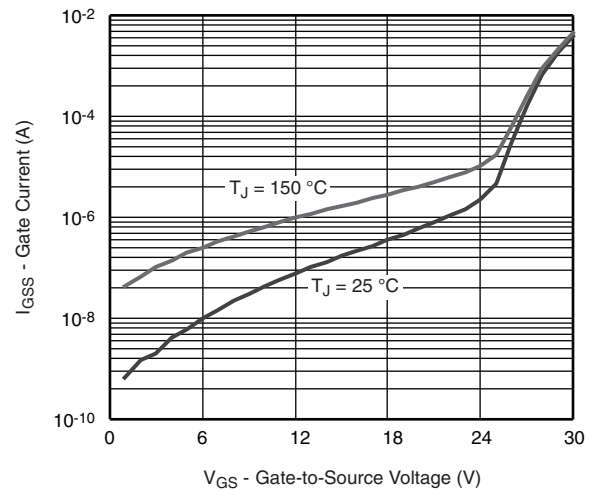
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

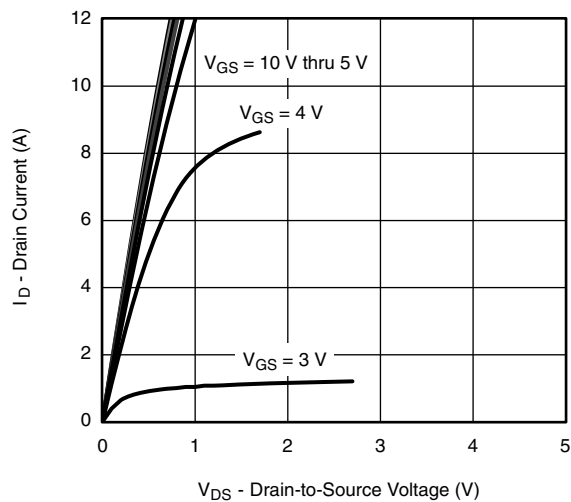
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



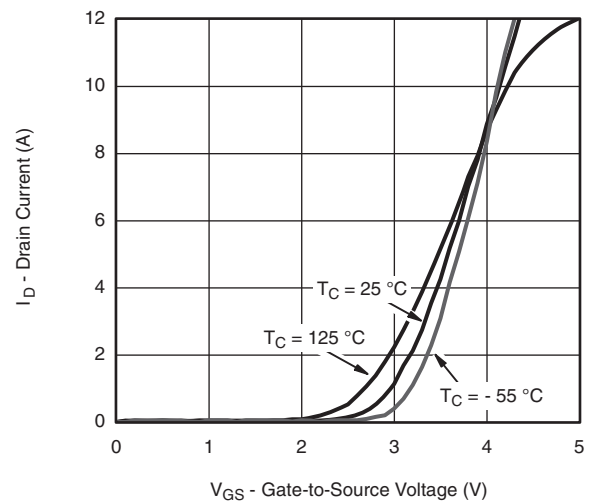
Gate Current vs. Gate-Source Voltage



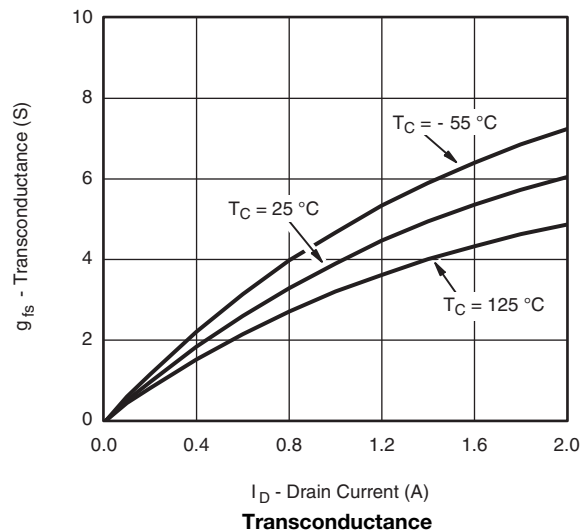
Gate Current vs. Gate-Source Voltage



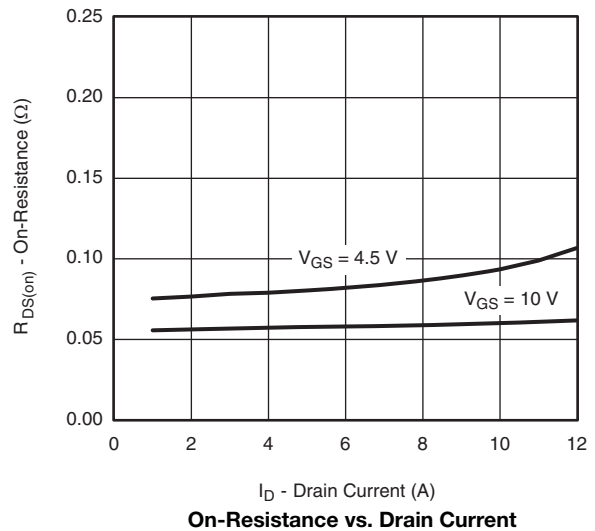
Output Characteristics



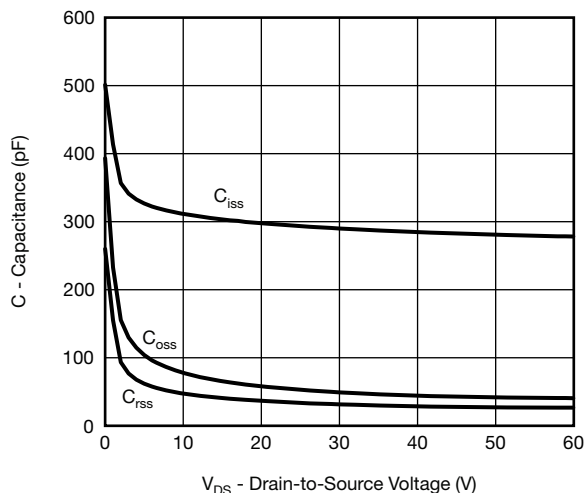
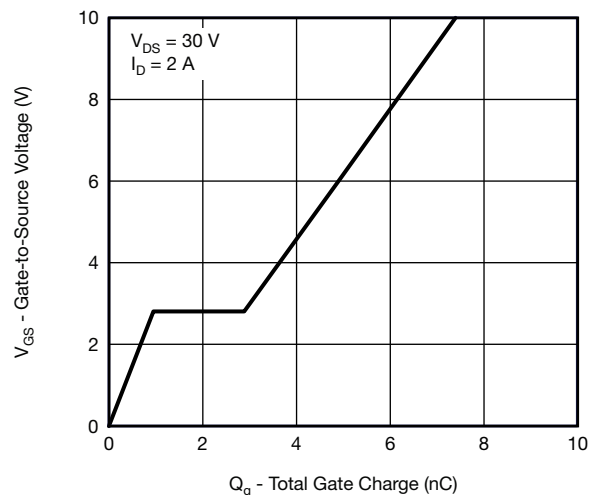
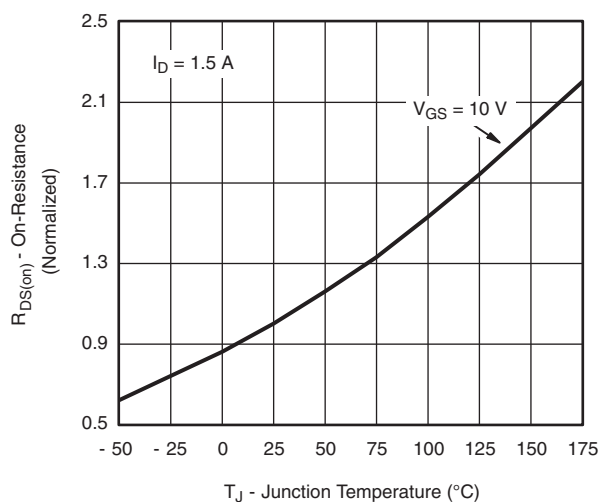
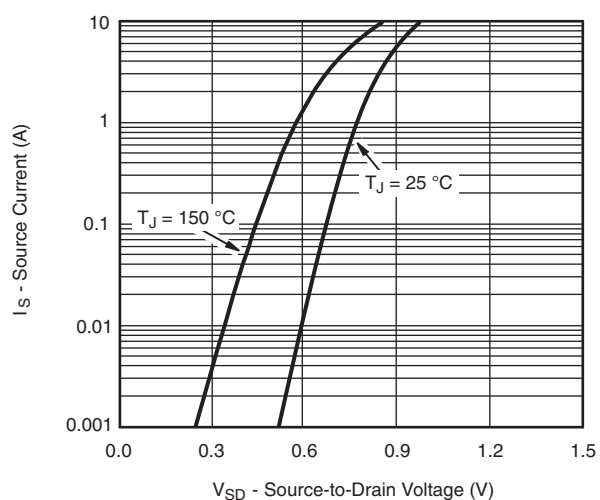
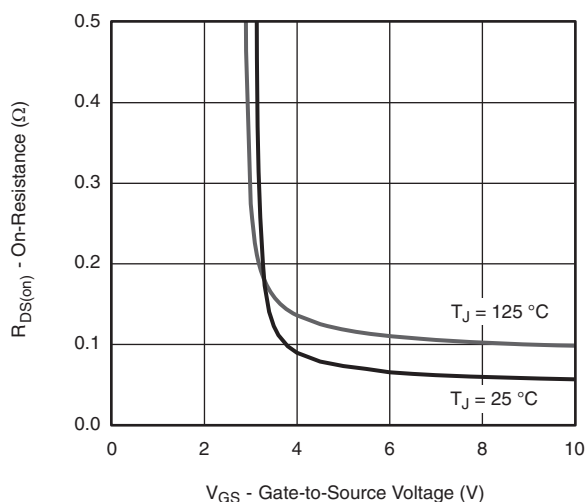
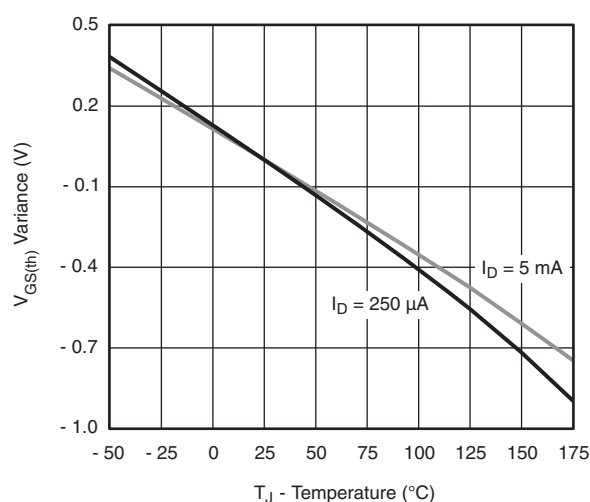
Transfer Characteristics



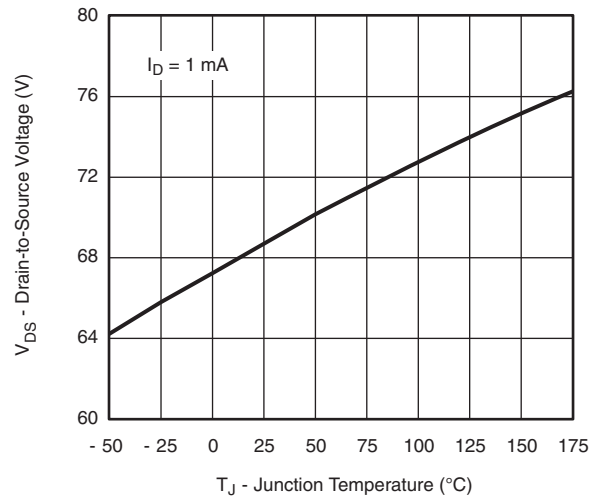
Transconductance



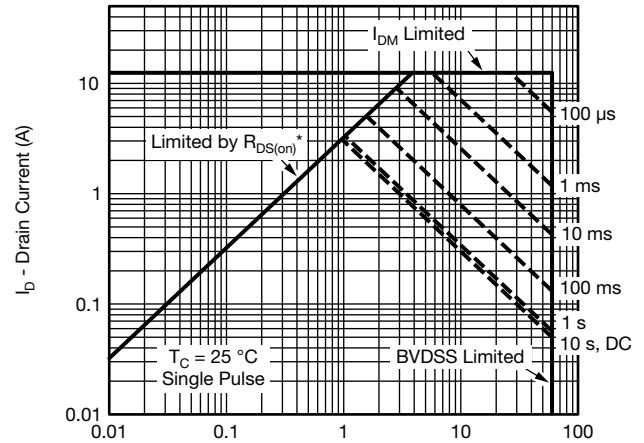
On-Resistance vs. Drain Current

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-Source Voltage

Threshold Voltage

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



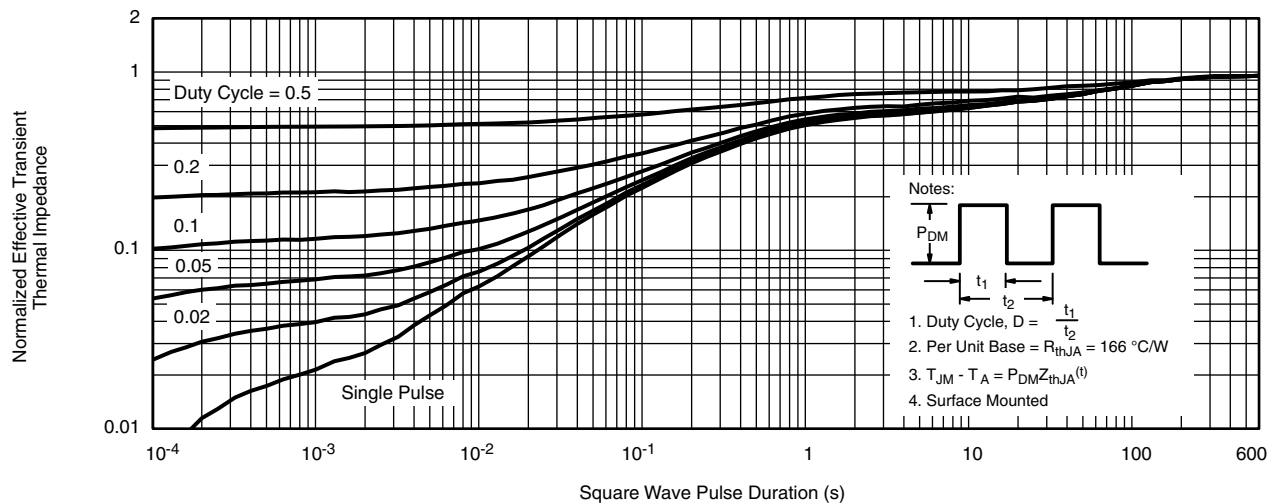
Drain-Source Breakdown vs. Junction Temperature



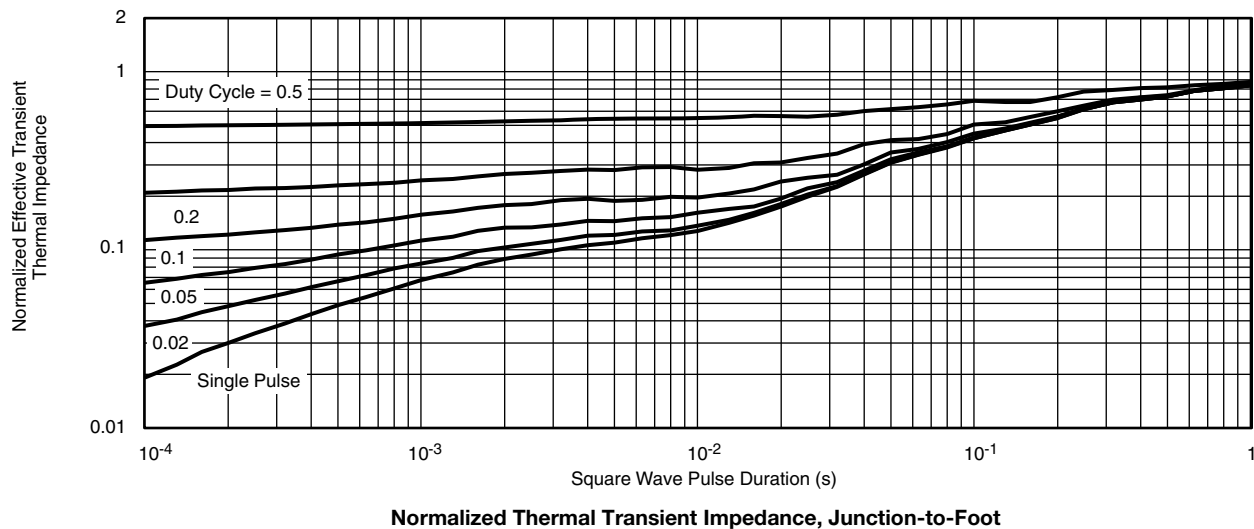
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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